

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the application of:

Atsushi KUROKAWA et al.

Appln. No.:

Filed: HERewith

For: METHOD FOR MANUFACTURING SEMICONDUCTOR DEVICE

\* \* \*

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

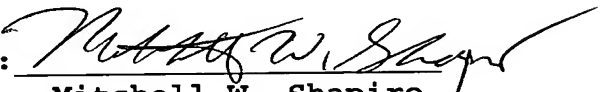
Sir:

Applicants wish to make of record the documents cited in prior Application No. 10/347,806 filed January 22, 2003, whether cited by Applicants or by the Patent Office. The documents are listed on the attached Form PTO-1449.

Respectfully submitted,

MWS:sjk

Miles & Stockbridge P.C.  
1751 Pinnacle Drive  
Suite 500  
McLean, Virginia 22102-3833  
(703) 903-9000

By:   
Mitchell W. Shapiro  
Reg. No. 31,568

September 30, 2003

<b>FORM PTO-1449</b>				<b>Atty. Docket No.</b> <b>XA-9801A</b>		<b>Appln. No.</b>	
<b><u>LIST OF DOCUMENTS CITED BY APPLICANT</u></b>							
				<b>Applicant</b> <b>Atsushi KUROKAWA et al.</b>			
				<b>Filing Date</b> <b>HEREWITH</b>		<b>Group</b>	
<b>U.S. PATENT DOCUMENTS</b>							
<b>Examiner Initial</b>		<b>Document Number</b>	<b>Date</b>	<b>Name</b>	<b>Class</b>	<b>Sub-class</b>	<b>Filing Date</b>
	AA	5,077,231	12/31/91	Plumton et al.	438	170	
	AB	5,166,083	11/24/92	Bayraktaroglu	438	170	
	AC	5,268,315	12/07/93	Prasad et al.	438	314	
	AD	5,324,671	06/28/94	Bayraktaroglu	438	317	
	AE	5,672,522	09/30/97	Streit et al.	438	312	
	AF						
	AG						
	AH						
	AI						
<b>FOREIGN PATENT DOCUMENTS</b>							
<b>Examiner Initial</b>		<b>Document Number</b>	<b>Date</b>	<b>Country</b>	<b>Class</b>	<b>Sub-class</b>	<b>Translation</b>
	AJ	2001-210723	08/03/01	Japan			<b>Abstract</b>
	AK						
	AL						
	AM						
	AN						
	AO						
<b>OTHER</b> (including author, title, date, pertinent pages, etc.)							
	AP	Chen et al., "High-Speed InGaP/GaAs HBT's Using a Simple Collector Undercut Technique to Reduce Base-Collector Capacitance," <u>IEEE Electron Device Letters</u> , Vol. 18, No. 7, July 1997, pp. 355-357.					
	AQ	Ahmari et al., "InGaP/CaAs Heterojunction Bipolar Transistor Grown on a Semi-Insulating InGaP Buffer Layer," <u>IEEE Electron Device Letters</u> , Vol. 18, No. 11, November 1997, pp. 559-561.					
	AR						
<b>Examiner</b>				<b>Date Considered</b>			
<b>EXAMINER:</b> Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.							